

Low $V_{CE(sat)}$ Transistor ($-20V$, $-3A$) 2SB1424 / 2SA1585S

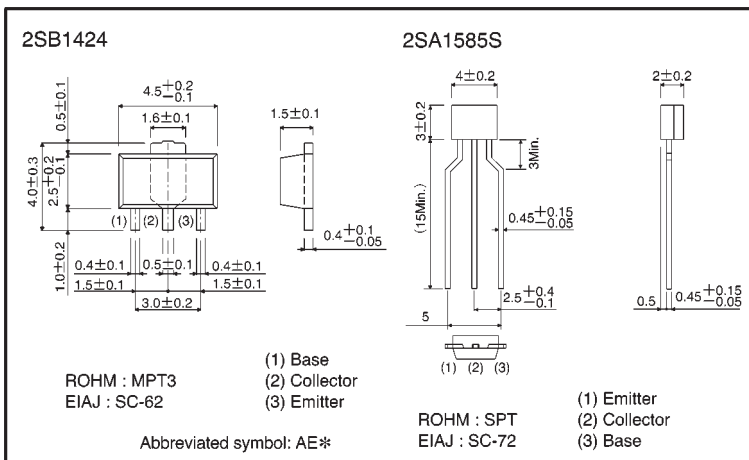
●Features

- 1) Low $V_{CE(sat)}$.
 $V_{CE(sat)} = -0.2V$ (Typ.)
($I_c/I_b = -2A / -0.1A$)
- 2) Excellent DC current gain characteristics.
- 3) Complements the 2SD2150 / 2SC4115S.

●Structure

Epitaxial planar type
PNP silicon transistor

●External dimensions (Units: mm)



* Denotes hFE

●Absolute maximum ratings ($T_a = 25^\circ C$)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	-20	V
Collector-emitter voltage	V_{CEO}	-20	V
Emitter-base voltage	V_{EBO}	-6	V
Collector current	2SB1424	-3	A
	2SA1585S	-2	
	I_{CP}	-5	A (Pulse) *
Collector power dissipation	2SB1424	0.6	W
	2SA1585S	0.4	
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 ~ +150	$^\circ C$

* Single pulse $P_w = 10ms$

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CB0}	-20	—	—	V	I _c =-50 μA
Collector-emitter breakdown voltage	BV _{CE0}	-20	—	—	V	I _c =-1mA
Emitter-base breakdown voltage	BV _{EB0}	-6	—	—	V	I _E =-50 μA
Collector cutoff current	I _{cB0}	—	—	-0.1	μA	V _{CB} =-20V
Emitter cutoff current	I _{EB0}	—	—	-0.1	μA	V _{EB} =-5V
Collector-emitter saturation voltage	V _{CE (sat)}	—	—	-0.5	V	I _c /I _B =-2A/-0.1A
DC current transfer ratio	h _{FE}	120	—	390	—	V _{CE} =-2V, I _c =-0.1A
Transition frequency	f _T	—	240	—	MHz	V _{CE} =-2V, I _E =0.5A, f=100MHz
Output capacitance	C _{ob}	—	35	—	pF	V _{CB} =-10V, I _E =0A, f=1MHz

●Packaging specifications and f_{FE}

Type	h _{FE}	Package	Taping	
		Code	TP	T100
		Basic ordering unit (pieces)	5000	1000
2SA1585S	QR	○	—	—
2SB1424	QR	—	○	—

h_{FE} values are classified as follows :

Item	Q	R
h _{FE}	120~270	180~390

●Electrical characteristic curves

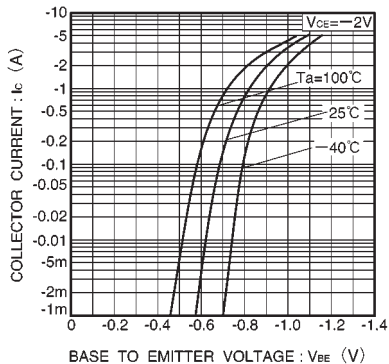


Fig.1 Grounded emitter propagation characteristics

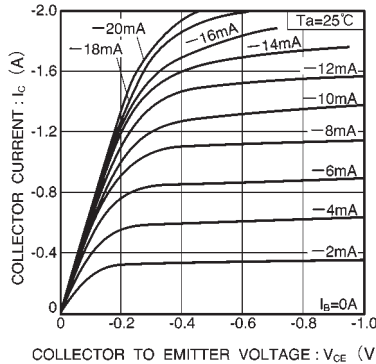


Fig.2 Grounded emitter output characteristics (I)

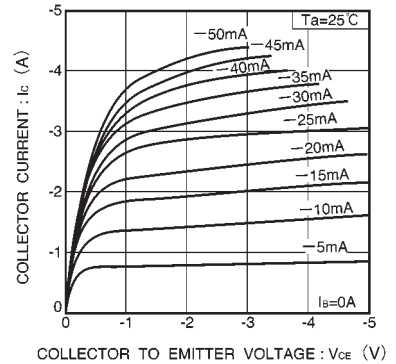


Fig.3 Grounded emitter output characteristics (II)

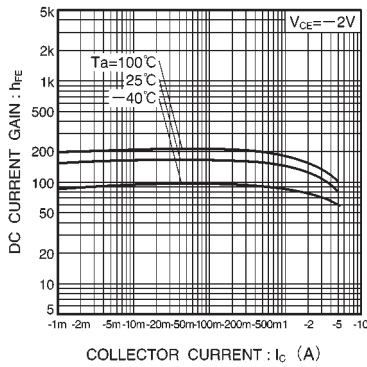


Fig.4 DC current gain vs. collector current

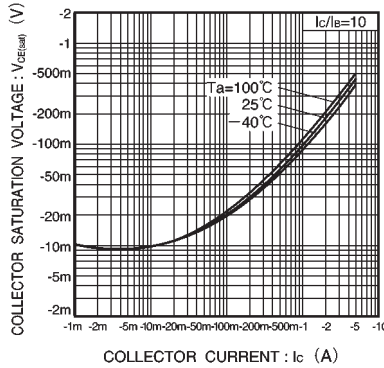


Fig.5 Collector-emitter saturation voltage vs. collector current (I)

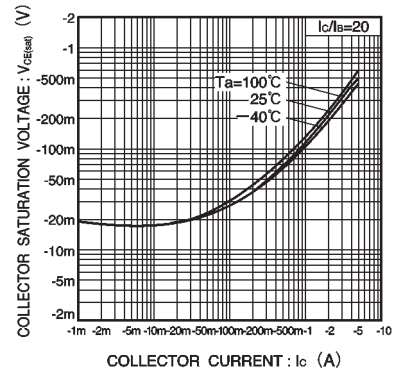


Fig.6 Collector-emitter saturation voltage vs. collector current (I)

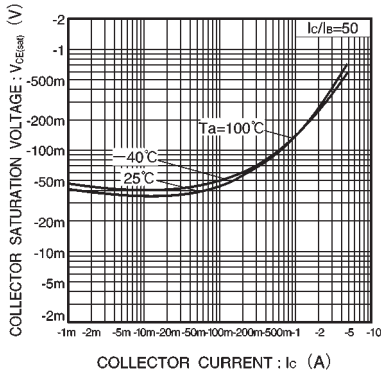


Fig.7 Collector-emitter saturation voltage vs. collector current (III)

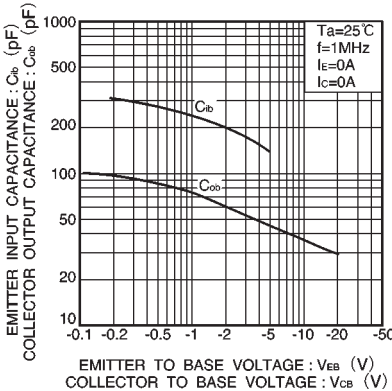


Fig.8 Gain bandwidth product vs. emitter current
Collector output capacitance vs. collector-base voltage

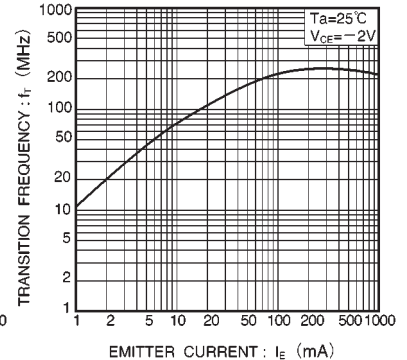


Fig.9 Emitter input capacitance vs. emitter base voltage